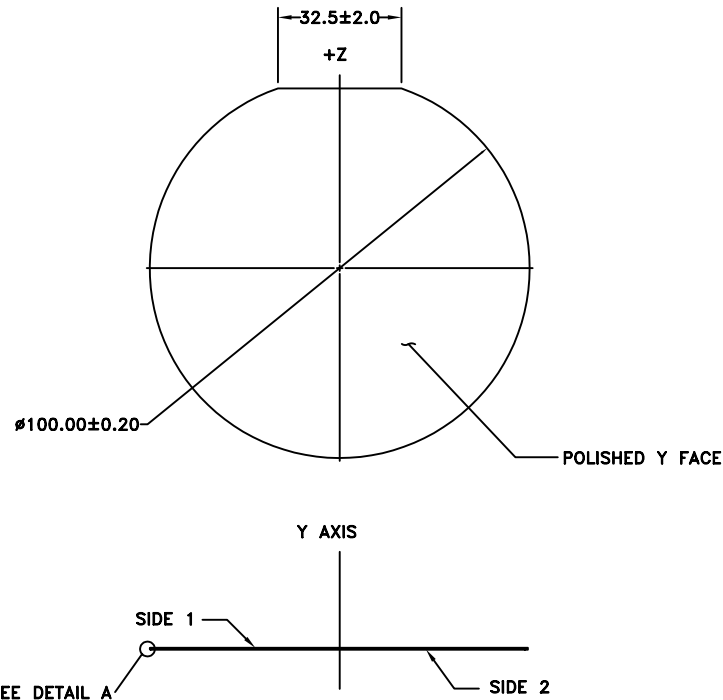


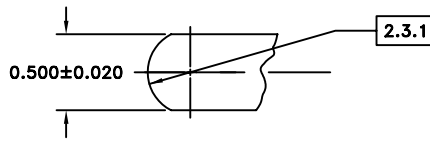
NOTES:

- 1.0.0 ORIENTATIONS
- 1.1.0 WAFER SURFACE IS NORMAL TO THE Y AXIS ±0.20°
- 1.2.0 PRIMARY FLAT, PERPENDICULAR TO THE Z AXIS ±0.20°.
- 2.0.0 SURFACES
- 2.1.0 SIDE 1
- 2.1.1 POLISHED, NO PITS OR SCRATCHES ALLOWED WITHIN THE WORKING AREA (ENTIRE WAFER DIAMETER LESS 1.0mm AROUND THE EDGE). INSPECTED USING UNAIDED EYE WITH REFLECTED LIGHT.
- 2.2.0 SIDE 2
- 2.2.1 GROUND, Ra 0.4um - 0.6um.
- 2.3.0 EDGE
- 2.3.1 ALL EDGES ROUNDED WITH A R=0.30±0.08mm RADIUS.
- 2.3.2 NO CHIPS GREATER THAN 0.5mm IN PENETRATION AND 1.0mm IN LENGTH.
- 2.4.0 FLATNESS
- 2.4.1 WARP < 50.0um. MEASURED IN THE FREE STATE.
- 2.4.2 TTV < 25.0um. DEFINED AS THE DIFFERENCE BETWEEN THE LOWEST AND HIGHEST ELEVATION OF THE WAFER, MEASURED IN THE CLAMPED STATE.
- 3.0.0 MATERIAL:
- 3.1.0 INTERNAL OPTICAL TRANSMISSION AT 500 nm THROUGH WAFER SHALL BE >1% AND <12%

REVISIONS					
ZONE	REV	DESCRIPTION	ECO NO.	APPD.	DATE
ALL	A	WAS TWO FLATS	.	NGO	6/14/99



For Reference Only



DETAIL A
SCALE: 40X

FINISH: SEE NOTES		CONTRACT NUMBER		Crystal Technology, Inc. A Siemens Company
MATERIAL: LN		DR. TOM NGO 5/5/99		
SPEC. NO. 3.1.0		CHK.		TITLE: LN WAFER, 100ØX0.5mm BLACK YZ, ONE Z FLT
UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN MM		APPD.		
TOLERANCES		APPD.		SIZE: A
INCHES	MILLIMETERS	DESIGN ACTIVITY APPROVAL:		DWG. NO. 97-02483-01
.XX ± .01	X.XX ± 0.25	CUSTOMER APPROVAL:		REV. A
.XXX ± .005	X.XXX ± 0.125	DO NOT SCALE DRAWING		SCALE: N/A
.XXXX ± .0020	ANG ± .5°			SH. 1 OF 1

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